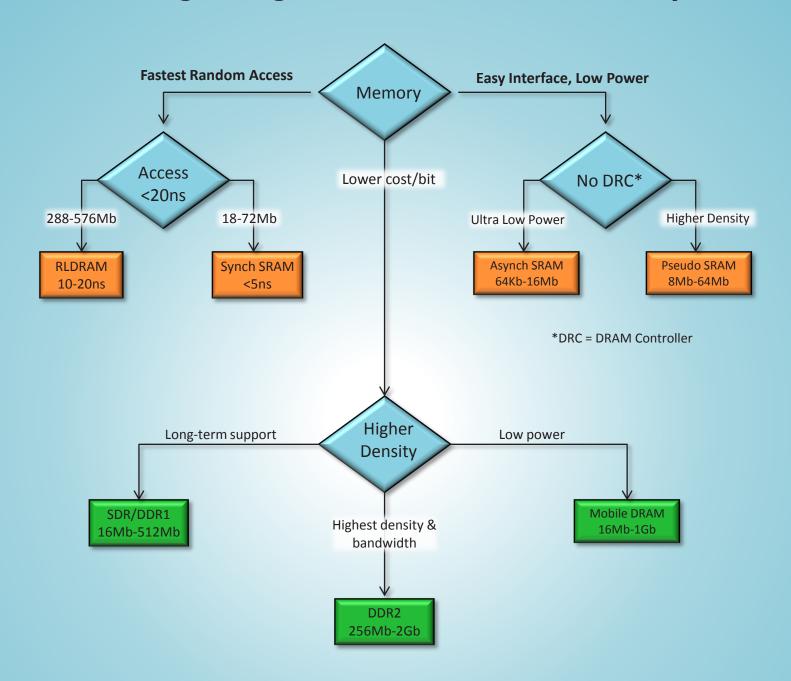
Selecting the Right ISSI Industrial Grade Memory



Long-Term Support from ISSI - replace other vendors End Of Life (EOL) products

Easy Cross Reference

Free Samples

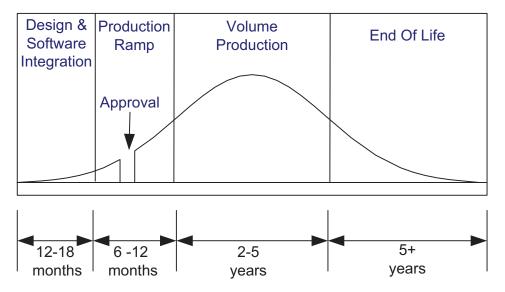
Special Support for Sync. SRAMs

Email part numbers for other vendors EOL product to find equivalent ISSI part number. Email: DRAM@issi.com or SRAM@issi.com

Request a free sample of the equivalent ISSI product

Save \$\$\$ by replacing Samsung EOL products with ISSI Synchronous SRAMs with no need for Last Time Buys or system redesigns

Industrial Systems Requiring Long-life Support for Memory



Typical Industrial System Product Life Cycle

High-mix, low volume industrial market segments have special needs in terms of industry specifications, strict qualification cycles, long-life requirements (without product changes permitted), and extremely long in-field use with the highest reliability standards expected.

The challenge for memory vendors is to ensure that by the end of the design cycle, they meet the requirement for long-term support covering extended production time with minimal design changes. ISSI's strategy is based on supporting our customer's needs for these long-life markets, so you can rely on ISSI for all your SRAM and DRAM needs.

Select ISSI for Your Industrial Memory Applications!

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Industrial Electronics Requirements	ISSI Solutions			
Long term support	7 to 10 years is typical life for an ISSI product			
Temperature Range: -40°C to +85°C	All ISSI products are designed and tested for industrial temperature			
Leaded Package Option	ISSI supports leaded package as well as ROHS			
x32 Organization	ISSI offers broadest range of x32 products and aligns with typical 32-bit embedded processors			
Support for 5V products	ISSI has 5V SRAMs and EDO/FP DRAMs			
Rugged products – high ESD tolerant	ISSI test all devices for HBM and MM. Min spec 2KV HBM			
Support for mature products	ISSI still support 64Kb SRAMs and all SDRAMs			
Roadmaps for long-term support	ISSI offers optional die shrink products for long term support & cost down roadmap			



Industrial Grade Memory Products

SDR Ordering Options

Density	Config.	Part Number ⁽¹⁾	Packa	age	Tempe	erature	Grade
			TSOP2	BGA	Com.	Ind.	Auto.
16Mbit	1M x 16	IS42S16100E, IS42S16100F					
CANALIA	4M x 16	IS42S16400F, IS42S16400J	•	•			
64Mbit	2M x 32	IS42S32200E, (IS42S32200L)	•	•			
	16M x 8	IS42S81600E, (IS42S81600F)	•		•		•
128Mbit	8M x 16	IS42S16800E, (IS42S16800F)	•	•	•	-	
	4M x 32	IS42S32400E, (IS42S32400F)	•	•	•	•	•
	32M x 8	IS42S83200D, (IS42S83200G)	•	•	•	-	
256Mbit	16M x 16	IS42S16160D, (IS42S16160G)	•	•			
	8M x 32	IS42S32800D, (IS42S32800G)	•	•	•		
	64M x 8	IS42S86400B, IS42S86400D	•		•		
512Mbit	32M x 16	IS42S16320B, IS42S16320D	•	•	•		•
	16M x 32	IS42S32160C, (IS42S32160D)		•	•	-	

DDR Ordering Options

Density	Config	Part Number ⁽¹⁾		Package		Tempe	erature (Grade
Delisity	Config.	Part Number	TSOP2-66	BGA-60	BGA-144	Com.	Ind.	Auto.
64Mbit	4M x 16	IS43R16400B				•	-	
128Mbit	8M x 16	IS43R16800CC, (IS43R16800E)						
120IVIDIL	4M x 32	IS43R32400D, (IS43R32400E)						
	32M x 8	IS43R83200B, (IS43R83200D)	-			•		
256Mbit	16M x 16	IS43R16160B, (IS43R16160D)		•		•		•
	8M x 32	IS43R32800B, (IS43R32800D)			•		•	•
	64M x 8	IS43R86400D		•				
512Mbit	32M x 16	IS43R16320D					-	
	16M x 32	IS43R32160D					-	

Mobile DDR Ordering Options

Density	Config.	Part Number
32Mbit	2M x 16	IS43LR16200C
SZIVIDIL	1M x 32	IS43LR32100C
64Mbit	4M x 16	IS43LR16400B
04WDIL	2M x 32	IS43LR32200B
128Mbit	8M x 16	IS43LR16800F
120Mbit	4M x 32	IS43LR32400F
256Mbit	16M x 16	(IS43LR16160F)
250101011	8M x 32	(IS43LR32800F)
512Mbit	32M x 16	IS43LR16320B
3 IZIVIDIL	16M x 32	IS43LR32160B

Mobile SDRAM Ordering Options

Density	Config.	Part Number
16M	1M x 16	IS42xx16100G
32M	2M x 16	IS42xx16200C
SZIVI	1M x 32	IS42xx32100C
64M	4M x 16	IS42xx16400K
04101	2M x 32	IS42xx32200K
128M	8M x 16	IS42xx16800G
120IVI	4M x 32	IS42xx32400G
256M	16M x 16	IS42xx16160D, (IS42xx16160E)
250101	8M x 32	IS42xx32800D, (IS42xx32800E)
512M	32M x16	IS42xx16320D
312101	16M x 32	IS42xx32160C, IS42xx32160D

- 1. Automotive grade SDR part numbers begin with "IS45S" and Automotive grade DDR part numbers begin with "IS46R".
- 2. xx: VM for $V_{DD} = 1.8V$, RM for $V_{DD} = 2.5V$, SM for $V_{DD} = 3.3V$. Production alternatives may be available.
- 3. Part numbers in parenthesis are sampling. All others in mass production.
- 4. Automotive grade Mobile DDR part numbers begin with "IS46LR".

DDR2 SDRAM Product Features:

- Single supply voltage of 1.8V ± 0.1V
- SSTL_18 compatible inputs
- Bidirectional differential or single-ended data strobe option
- Data masking per byte on Write commands
- Programmable burst length of 4 or 8
- Programmable CAS Latency of 3, 4, 5 or 6

- Auto-Refresh and Self-Refresh Modes
- OCD (Off-Chip Driver Impedance Adjustment)
- ODT (On Die Termination) supported
- Package options: 126-ball BGA for x32, 84-ball BGA for x16, 60-ball BGA for x8
- Long-Term Support for all densities
- Industrial and Automotive grade temperatures

DDR2 SDRAM Ordering Options

Density	Config.	Part No.	Speeds	Pkg.	Ordering Options
	8Mx32	IS43DR32801A	DDR2-400B, DDR2-533C	BGA(126)	-5BBL, -5BBLI, -37CBL, -37CBLI
	8Mx32	IS46DR32801A	DDR2-400B	BGA(126)	-5BBLA1, -5BBLA2
256M	16Mx16	IS43DR16160A	DDR2-400B, DDR2-533C, DDR2-667D, DDR2-800E	BGA(84)	-5BBLI, -37CBL, -37CBLI, -3DBL, -3DBLI, -25EBL
	16Mx16	IS46DR16160A	DDR2-400B, DDR2-533C	BGA(84)	-5BBLA1, -37CBLA1, -5BBLA2
	32Mx8	IS43DR83200A	DDR2-533C	BGA(60)	-37CBLI
	32Mx16	IS43DR16320B	DDR2-533C, DDR2-667D, DDR2-800E, DDR2-800D	BGA(84)	-37CBL, -37CBLI, -3DBL, -3DBLI, -25EBL, -25EBLI, -25DBL, -25DBLI
512M	32Mx16	IS46DR16320B	DDR2-533C, DDR2-667D	BGA(84)	-37CBLA1, -3DBLA1, -37CBLA2, -3DBLA2
	64Mx8	IS43DR86400B	DDR2-533C, DDR2-667D, DDR2-800E, DDR2-800D	BGA(60)	-37CBLI, -3DBL, -3DBLI, -25EBLI, -25DBLI
	64Mx16	IS43DR16640A	DDR2-667D, DDR2-800E, DDR2-800D	BGA(84)	-3DBL, -3DBLI, -25EBL, -25EBLI, -25DBL, -25DBLI
1G	64Mx16	IS46DR16640A	DDR2-667D	BGA(84)	-3DBLA1, -3DBLA2
	128Mx8	IS43DR81280A	DDR2-667D, DDR2-800E, DDR2-800D	BGA(60)	-3DBL, -3DBLI, -25EBLI, -25DBLI
2G	128Mx16	IS43DR16128	DDR2-667D	BGA(84)	-3DBL, -3DBLI
26	128Mx16	IS46DR16128	DDR2-667D	BGA(84)	-3DBLA1, -3DBLA2

Notae:

- 1. Automotive grade DDR2 part numbers begin with "IS46DR".
- 2. Contact ISSI for other ordering options.

RLDRAM® Memory

Reduced Latency (RL) DRAM is a low-latency, high-bandwidth memory technology that is designed for high-performance applications such as networking, test equipment and other performance critical applications

Density	Common I/O / Separate I/O	Config.	Part Number
	SIO	x9	IS49NLS93200
	810	x18	IS49NLS18160
288Mbit		x9	IS49NLC93200
	CIO	x18	IS49NLC18160
		x36	IS49NLC36800
	SIO	x9	IS49NLS96400
	\$IO	x18	IS49NLS18320
576Mbit		x9	IS49NLC96400
	CIO	x18	IS49NLC18320
		x36	IS49NLC36160

Notes:

- 144-ball BGA Package: Leaded/Lead-free
- Temperature grades: Commercial/Industrial
- Speeds: 300MHz, 400MHz
- · RLDRAM is a registered trademark of Micron, Technology, Inc.

Issi Industrial Grade Memory Products

Asynchronous SRAMs

Density	Config.	Legacy	High Speed	Ultra Low Power	PSRAM/CRAM
64Kb	x8	•			
256Kb	x8				
512Kb	x16				
1Mb	x8				
TIVID	x16				
2Mb	x8		•		
ZIVID	x16		•		
4Mb	x8	•	•		
TIVID	x16	•	•		
	x8	•	•		
8Mb	x16	•	•	•	•
	x32		•		
	x8		•		
16Mb	x16		•		•
	x32		•		
32Mb	x16				•
64Mb	x16				•

■ = High Speed Product ■ = High Speed + Low Power options

■ = Ultra Low Power

Voltage*	5V	1.65-3.6V	1.65-3.6V	1.8V, 2.7-3.6V PSRAM 1.8V CRAM
Speed*(typ)	HS 10-12ns LP 25-55ns	HS 8-20ns LP 25-35ns	35-55ns	70ns
Package(s)*	SOJ TSOP BGA (8Mb only)	SOJ TSOP mBGA	SOJ TSOP mBGA	TSOP (8Mb only) BGA(48) PSRAM BGA(54) CRAM

^{*}Check datasheets for specific part number.

Synchronous SRAMs

Density	Config.	PipeLine / Flow Through	No Wait (equiv to ZBT™)	QUAD / DDR-II	QUADP / DDR-IIP†
	x18		•		
2Mb	x32		•		
	x36		•		
	x18				
4Mb	x32				
	x36				
	x18				
8Mb	x32				
	x36				
	x18				
18Mb	x36				
	x72				
36Mb	x18				•
Solvid	x36			•	•
72Mb	x18				
721010	x36			•	•
Volta	age*	3.3V/2.5V	3.3V/2.5V	1.8V	1.8V
Spe	ed*	133-250 MHz	133-250 MHz	250-333MHz	300-550MHz
Packa	ge(s)*	TQFP PBGA BGA	TQFP PBGA BGA	BGA(165)	BGA(165)

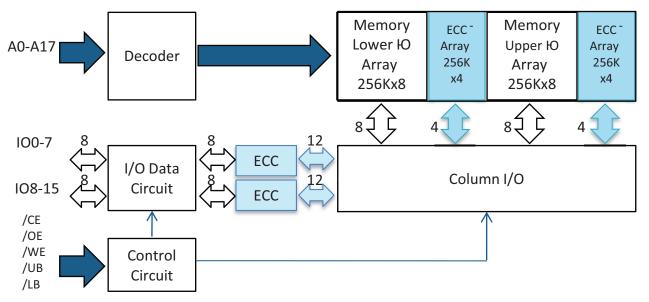
[†]Equivalent to QDRTM/QDR-II and DDR/DDR-II

ZBT is a trademark of Integrated Device Technology Inc. QDR SRAM is a trademark of the QDT Consortium

Innovative Design Reinforces ISSI's Long-Term Commitment to SRAMs

Error Correction Code (ECC) High Speed Low Power SRAMs

This first Error Correction Code (ECC) based Asynchronous SRAM meets high quality requirements in automotive, industrial, military-aerospace, and other applications.



Features:

- Independent ECC with hamming code for each byte
- Detect and correct one bit error per each byte
- Better reliability than parity code schemes which can only detect an error but not correct an error
- Backward Compatible: Drop in replacement to current in industry standard devices (without ECC)
- 2Mb, 4Mb, 8Mb Asynch SRAMs products
- Synchronous SRAM products in design

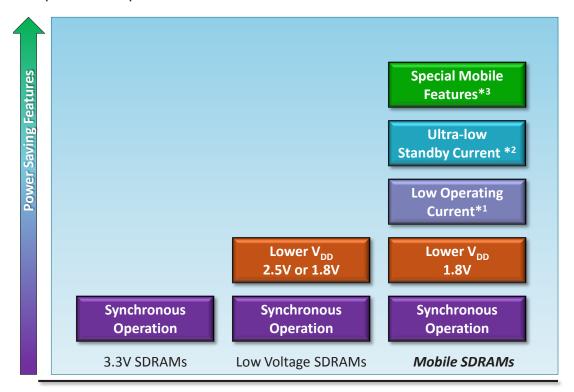
Ultra Low Power SRAMs

ISSI's family of Ultra-Low Power (ULP) SRAMs offer significant power savings compared to other versions. Products are offered in densities of 1Mb, 2Mb, 4Mb, 8Mb and 16Mb, with options for x8 or x16 in a range of package types.

	IS62WV1288DBLL 128Kx8 Ultra Low Power	IS65WV1288DBLL 128Kx8 Ultra Low Power	Comments
Temperature Support	Industrial (-40°C to +85°C)	Automotive (-40°C to +125°C)	
Standby Current	4 μΑ	18 μΑ	Typical value 0.6 μA
Operating Current	8 mA	12 mA	Typical value 4 mA BEST in the INDUSTRY!
Data Retention Current	4 μΑ	18 μΑ	Typical value 0.5 μA
Packaging	TSOP-I (32 pins) sTSOP (32 pins) SOP (32 pins) BGA (36 pins)	TSOP-I (32 pins) sTSOP (32 pins) SOP (32 pins) BGA (36 pins)	Lead-free and Leaded, RoHS Compliant
Speed	45 ns**	45 ns	** 35ns Refer to datasheet

Mobile SDRAMs - Ideal for Power Sensitive Applications

ISSI's Low Power Mobile SDRAMs are ideal for applications where both high performance and low power consumption are important.



- *1. Mobile SDRAM Operating Current typically 33-50% lower than standard SDRAM
- *2. Mobile SDRAM Standby Current typically 90% lower than standard SDRAM
- *3. Special Mobile Features reduce power even more!

Mobile Features

Temperature Compensated Self Refresh (TCSR)	Adjust refresh rate based on temperature to minimize power consumption at lower temperatures
Partial Array Self Refresh (PASR)	Eliminates unnecessary refresh to minimize power
Deep Power Down (DPD)	Lowest power state when data retention is not required
Drive Strength (DS)	Adjust output drive to actual bus loading to minimize power

Chipset Support for Memory Types

Chipset		SRAM			DRAM			
		Asynch.	Synch	Pseudo	SDR/DDR	LP DDR	DDR2	RLDRAM
FPGA	Low-Mid End	•		•	•	•		•
	High End	•		•	•	•		•
ASIC		•		•	•			
MCU	Low-End (no DRC)	•						
	High End	•			•	•		
MPU		•		•	•			
DSP						•		
Network Processor			•				•	•

Industrial Grade Memory Products

